

	Hit s	Search Text	DBs
15	0	((low\$3k or dielectric or silicon\$5nitride or SiON or (low\$4 near16 dielectric) or SSQ or silsesquioxane) near22 (heat\$9 or bak\$4 or anneal\$4 or cur\$3) near40 (eliminat\$4 or dissipat\$5 or reduc\$4 or (drive near2 off) or (rid\$4)) near19 (contaminant\$4 or water or poison\$6 or volatil\$5)) and (low\$3k near9 dieletric)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
16	0	((low\$3k or dielectric or silicon\$5nitride or SiON or (low\$4 near16 dielectric) or SSQ or silsesquioxane) near22 (heat\$9 or bak\$4 or anneal\$4 or cur\$3) near40 (eliminat\$4 or dissipat\$5 or minimi\$5 or reduc\$4 or (drive near2 off) or (rid\$4)) near19 (contaminant\$4 or water or poison\$6 or volatil\$5)) and (low\$3k near9 dieletric)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
17	300	((low\$3k or dielectric or silicon\$5nitride or SiON or (low\$4 near16 dielectric) or SSQ or silsesquioxane) near22 (heat\$9 or bak\$4 or anneal\$4 or cur\$3) near40 (eliminat\$4 or dissipat\$5 or minimi\$5 or reduc\$4 or (drive near2 off) or (rid\$4)) near19 (contaminant\$4 or water or poison\$6 or volatil\$5))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB